

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

- SUB 7
F1
- 1-10. (Withdrawn)
11. (Canceled) ✓
- E1
- 12-30. (Withdrawn)
31. (Previously Amended) A semiconductor device comprising:
a first substrate comprising a circuit comprising a thin film transistor;
a second substrate opposing said first substrate;
a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit; and
an insulating film in contact with a side surface of said metallic film,
wherein said connecting wiring and said insulating film are formed over said first substrate,
wherein said insulating film is formed along with the length direction and the width direction of said lamination film, and
wherein said connecting wiring has a taper shape.
32. (Previously Amended) A semiconductor device of claim 31 wherein the insulating film is formed of the same materials as that of an insulating film between a gate wiring and a source wiring of the thin film transistor.
33. (Previously Amended) A semiconductor device of claim 31 wherein said connecting wiring is electrically connected to a wiring of a third substrate via an anisotropic conductive film.

34. (Canceled)

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35. (Previously Amended) A semiconductor device of claim 31 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

36. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 31 wherein the metallic film comprises Al.

37. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 31 wherein the metallic film comprises W.

38. (Currently Amended) A [contact structure] semiconductor device of claim 31 wherein the metallic film is a lamination film formed of a W layer and a layer comprising W and N.

39. (Previously Amended) A semiconductor device of claim 31 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

40. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 31 wherein the transparent conductive film comprises zinc oxide.

41. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 31 wherein the transparent conductive film comprises zinc oxide and indium oxide.

42. (Original) The device of claim 31 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

43. (Previously Amended) A semiconductor device comprising:
a first substrate comprising a circuit comprising a thin film transistor;
a second substrate opposing said first substrate;

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a connecting wiring comprising a metallic film and a transparent conductive film in contact with said metallic film for connecting said circuit to another circuit;
a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate; and
an insulating film in contact with a side surface of said metallic film comprising the same material as that of the column-shape spacer,
wherein said connecting wiring, said column spacer, and said protecting film are formed over said first substrate,
wherein said insulating film is formed along with the length direction and the width direction of said lamination film, and
wherein said connecting wiring has a taper shape.

44. (Previously Amended) A semiconductor device of claim 43 wherein said connecting wiring is electrically connected to a wiring of a third substrate via an anisotropic conductive film.

45. (Canceled)

46. (Previously Amended) A semiconductor device of claim 43 wherein a thickness of the metallic film is between 100 nm and 1 μ m.

47. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 43 wherein the metallic film comprises Al.

48. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 43 wherein the metallic film comprises W.

49. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 43 wherein the metallic film is a lamination film formed of a W layer and a layer comprising W and N.

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50. (Previously Amended) A semiconductor device of claim 43 wherein a thickness of the transparent conductive film is between 50 nm and 0.5 μ m.

51. (Currently Amended) A [contact structure] semiconductor device of claim 43 wherein the transparent conductive film comprises zinc oxide.

52. (Currently Amended) A ~~contact structure~~ semiconductor device of claim 43 wherein the transparent conductive film comprises zinc oxide and indium oxide.

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53. (Original) The device of claim 43 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

54. (Withdrawn)

55. (Original) A semiconductor device of claim 31 wherein the lamination film is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

56. (Original) A semiconductor device of claim 43 wherein the lamination film is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.
